

BD912

Rev. H Oct.-2018

TO-220

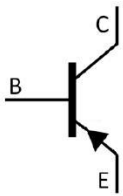
PNP

Silicon PNP transistor in a TO-220 Plastic Package.

, BD911

High V_{CEO} , high I_C , complement to BD911.

Use in power linear and switching applications.



PIN1 Base

PIN 2 Collector

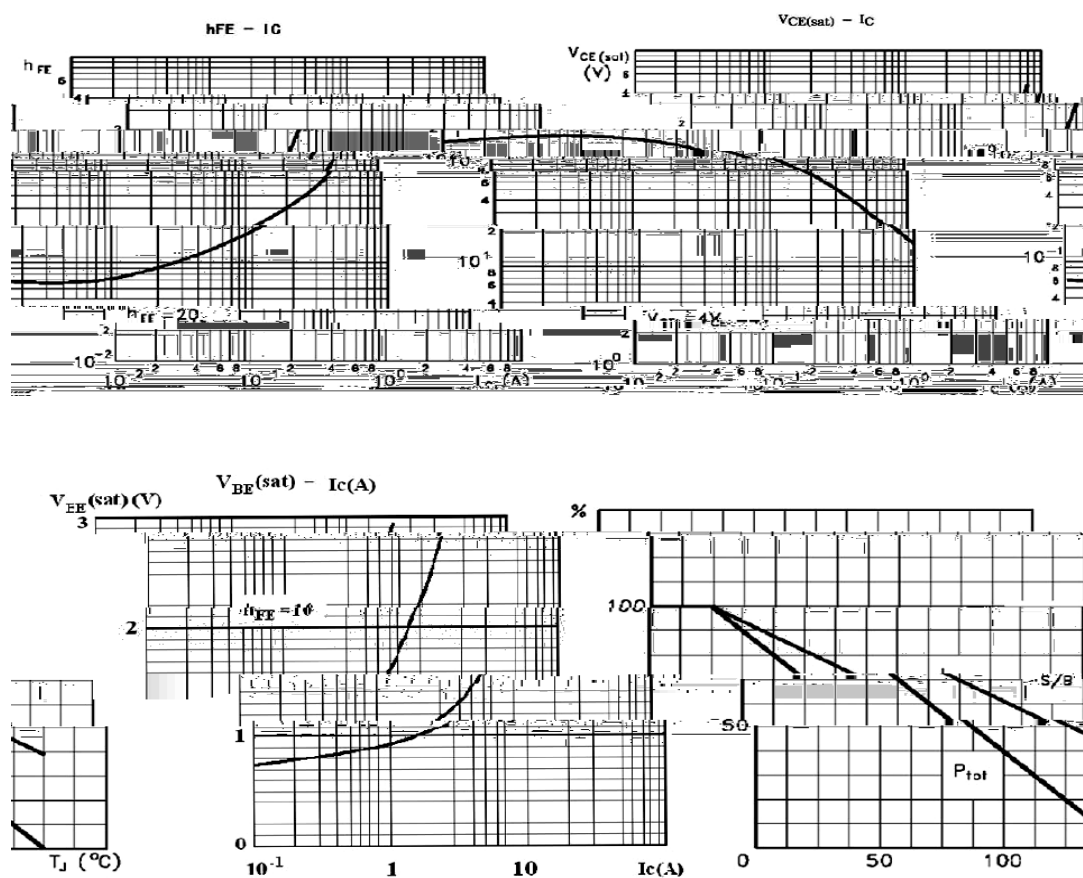
PIN 3 Emitter

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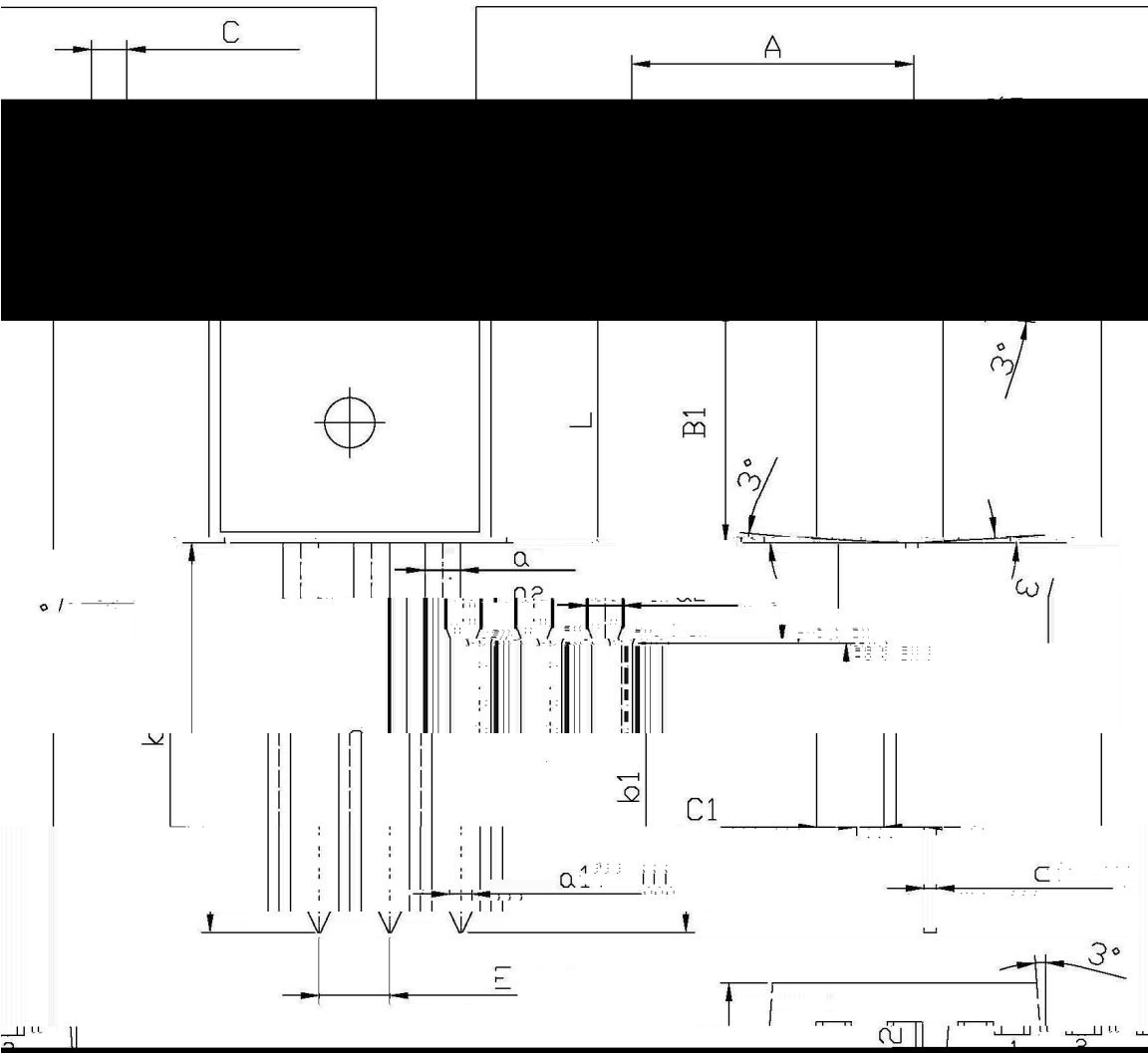
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-15	A
Base Current – Continuous	I_B	-5.0	A
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	90	W
Junction Temperature	T_j	150	

/ Electrical Characteristic Curve



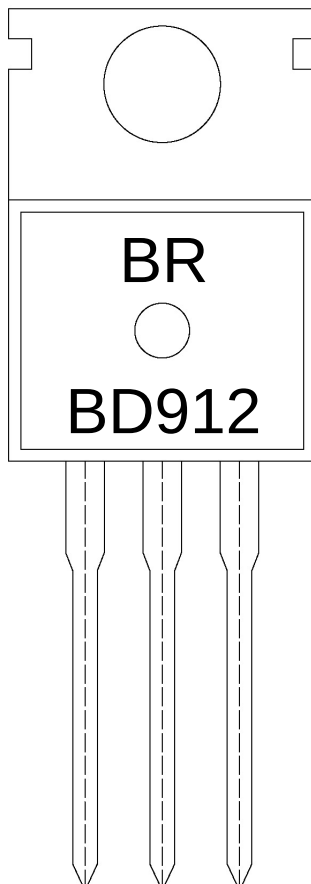
/ Package Dimensions

单位: mm TO-220



Dimensions in Millimeters			Dimensions in Millimeters		
Symbol	Min	Max	Symbol	Min	Max
1.4			9.8	10.2	1.2
0.7			3.50	3.64	0.3
15.7		16.1	B	9.0	9.4
0.7			0.9		0.1
0.4	0.6		1.22	1.32	
1.4			2.24	2.74	
			0.2	1.25	1.45

/ Marking Instructions



BR

BD912

Note:

BR: Company Code

BD912: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10 /sec.
- 1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱